

Si3404 データ・シート

完全統合型 IEEE 802.3 タイプ 1 準拠 POE PD インターフェイスとコンパクトな設置面積の高効率スイッチング・レギュレータ

Si3404 は、パワー・オーバー・イーサネット (PoE) 駆動デバイス (PD) アプリケーションに必要な電源管理および制御機能を統合しています。これらのデバイスは、10/100/1000BASE-T イーサネット接続を介して供給される高電圧を、調整された低電圧出力電源に変換します。このデバイスの最適化されたアーキテクチャにより、ソリューションの設置面積と外部部 BOM コストを最小限に抑え、低コストの外部コンポーネントを使用して高い性能を維持できます。Si3404 は過渡サージ・サプレッサを統合しています。また、スイッチング電源 FET および関連機能も統合しています。統合された電流モード制御スイッチング・レギュレータは、絶縁式または非絶縁式のフライバックおよびバック・コンバータ技術をサポートしています。レギュレータのスイッチング周波数は、シンプルな外部抵抗値で調整でき、不要な高調波を回避して放射を効果的に制御します。

このデバイスは、タイプ 1 の IEEE 802.3at 仕様の 1 イベント分類を完全にサポートしています。外部標準レジスタは、分類モードの検出機能とプログラミング用の IEEE 802.3 シグネチャを提供し、内部スタートアップ回路により、ホット・スワップ・スイッチおよび電圧レギュレータの適切に制御された初期ソフトスタート動作を保証します。

Si3404 は薄型、20 ピン、4 x 4 mm QFN パッケージで提供されます。

主な機能

- ・ タイプ 1 (PoE) 電力
- ・ IEEE 802.3at タイプ 1 に準拠
- ・ 電流モード DC-DC コンバータ
- ・ 調整可能なスイッチング周波数
- ・ 変圧器バイアス巻線のサポート
- ・ 補助アダプタ機能
- ・ 統合型ホット・スワップ FET とスイッチング FET
- ・ 120 V の絶対最大電圧性能
- ・ -40 ~ +85 °C の拡張温度範囲
- ・ ROHS 対応のコンパクトな 4 mm x 4 mm QFN パッケージ

アプリケーション

- ・ ボイス・オーバー IP 電話
- ・ ワイヤレス・アクセス・ポイント
- ・ セキュリティおよび監視 IP カメラ
- ・ POS 端末
- ・ インターネット・アプライアンス
- ・ ネットワーク・デバイス

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2. System Overview

The following Block Diagrams will give the designer a sense for the internal arrangement of functional blocks, plus their relationships to external pins. The Block Diagrams are followed by a description of the features of these integrated circuits.

2.1 Block Diagram

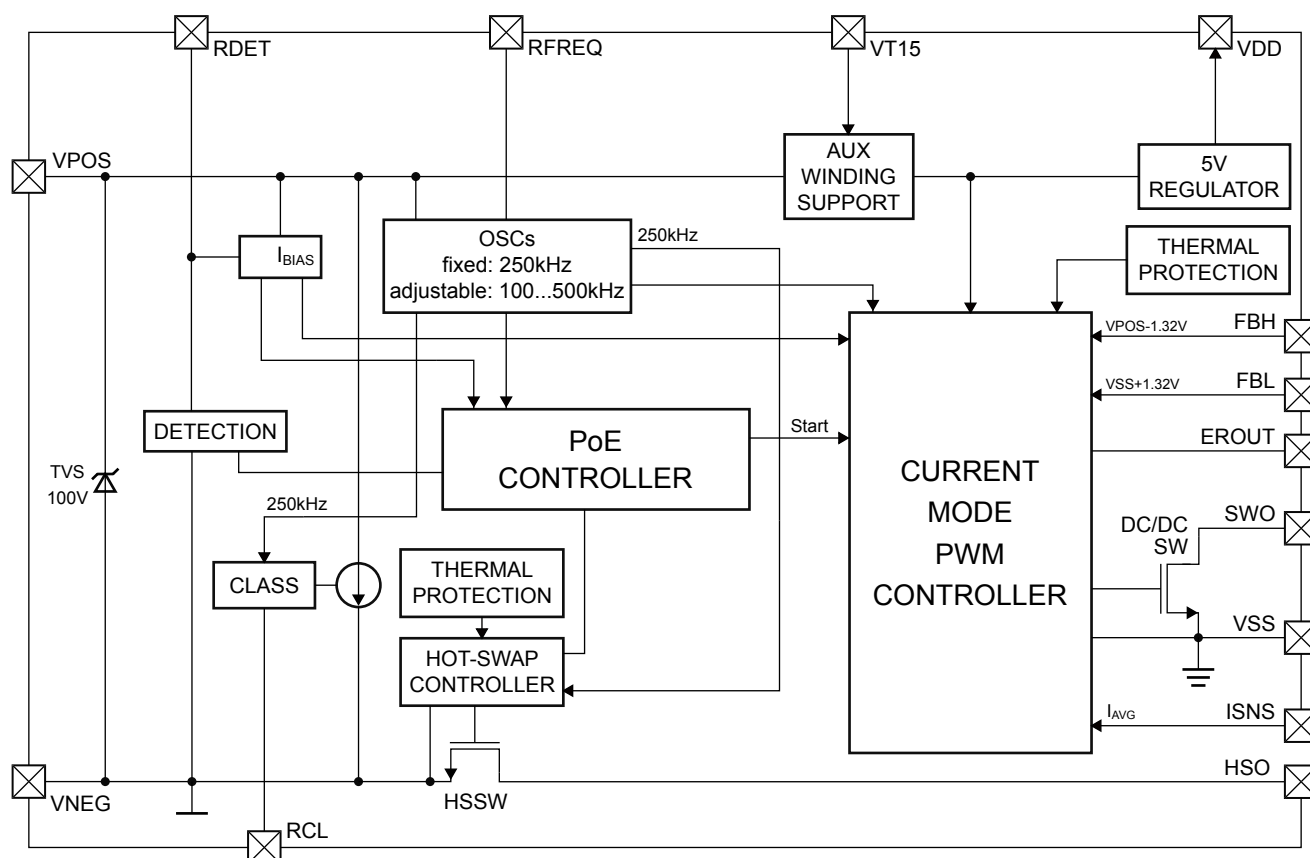


Figure 2.1. Si3404 Block Diagram

2.2 Power over Ethernet (PoE) Line-Side Interface

The PoE line interface consists of external diode bridges, internal surge protection, and protocol interface support for detection and classification.

The chip features active protection against surge transients and accidentally applied telephony voltages.

2.2.1 Surge Protection

The surge protection circuit is activated if the VPOS-VNEG voltage exceeds V_{PROT} and the hotswap switch is off (dc-dc is not powered). If the hotswap switch is on, the surge power is sunk in the dc-dc's input capacitance.

The internal surge protection can be overridden with an external TVS if higher than specified surge conditions need to be tolerated. The external surge device must be connected in parallel to the internal one; therefore, the designer must ensure that the external surge protection will activate prior to the internal surge protection.

2.2.2 Telephony Protection

The Si3404 provides protection against telephony ringing voltage. The telephony ringing is much longer than the surge pulse but it has less energy, therefore, the Si3404 has a switch parallel with the supply (between VPOS and VNEG). When the protection circuit is activated, it turns ON the protection switch; the ringing energy then dissipates on this switch and ringing generator resistance ($> 400 \Omega$).

2.2.3 Detection and Classification

When the Si3404 is connected via Ethernet cable to a PSE-enabled Ethernet switch, it has to provide a characteristic resistance (~25 k Ω) to the PSE in a given voltage range (2.7–10.1 V). This is called detection. After the PSE detects the PD, the PSE increases the voltage above the classification threshold 14.5 V. Then, the PD provides the classification current to inform the PSE about its required power class (Class 1, 2, 3, or 4). Type 1 PSEs cannot provide enough power for a Class 4 PD. Type 2 PSEs have additional voltage steps before switching on the PD. After an initial classification voltage pulse, the Type 2 PSE reduces the voltage below the mark threshold level (10 V) then raises it up again to the Class event range. Last, before switching ON the dc-dc, it reduces the voltage again.

The Si3404 is a Type 1 PD. The following figure represents the typical turning ON procedure of the PD, which includes detection, classification and PD turn ON.

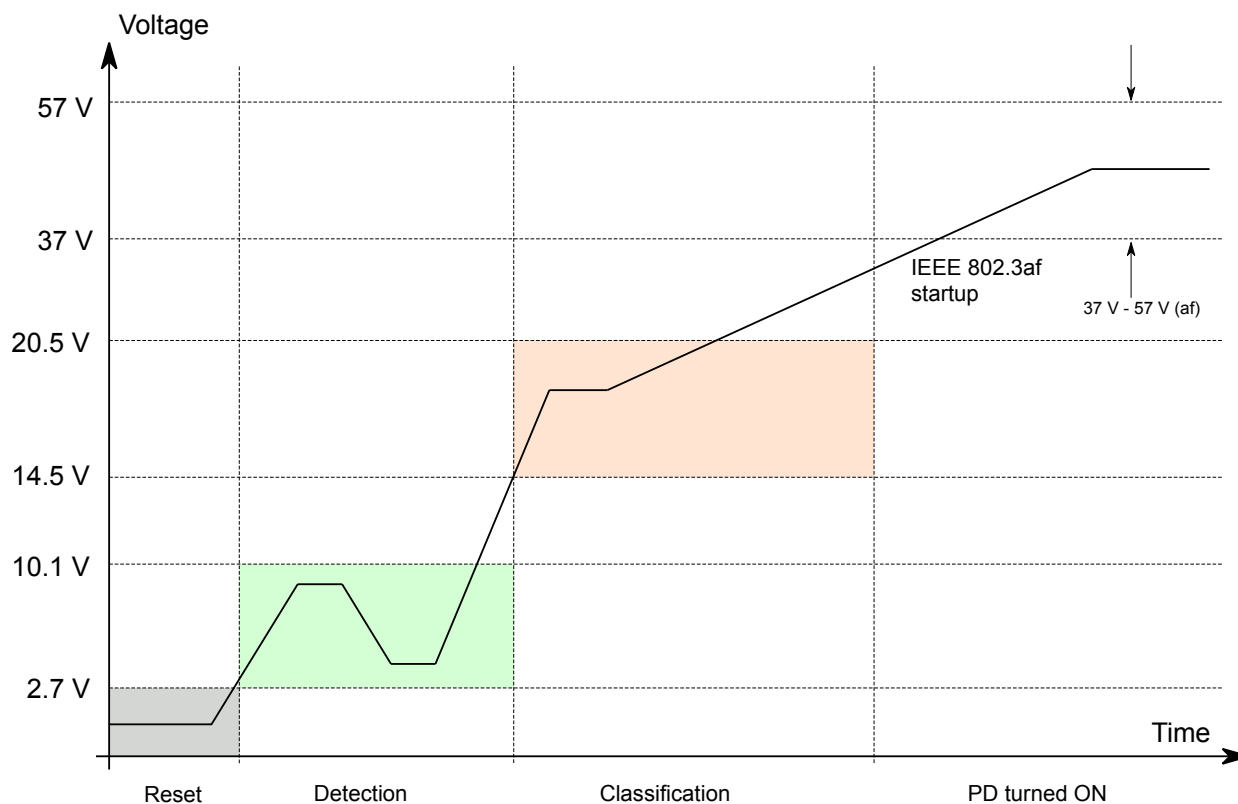


Figure 2.2. Powered Device Voltages

2.3 Hotswap Switch

The hotswap switch is a high voltage switch which separates the PoE interface from the dc-dc converter domain. The internal hotswap switch (HSSW) is turned on (conducting) when the PoE interface voltage goes above V_{UVLO_R} . It provides limited inrush current until the dc-dc side capacitor is charged. The hotswap switch turns off (open) if voltage on the HSSW switch is greater than V_{HSSW_OFF} .

In overload, the hotswap switch goes into current-limiting mode with a current limit of I_{OVL} . It will turn back ON after $T_{WAITHSSW}$ elapses and the dc-dc input capacitor is recharged, meaning the HSO-VNEG voltage is less than V_{HSSW_ON} .

2.4 HSSW State Machine

The HSSW operates as simple 4-state state machine:

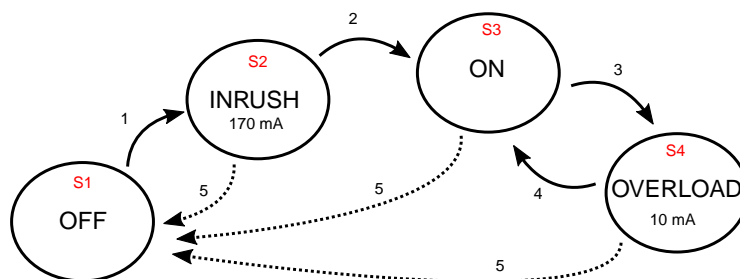


Figure 2.3. Hotswap Switch 4-State Machine

Transitions

1. UVLO released.
2. Input capacitor charged; PWM starts with Soft-Start protection.
3. Overcurrent detected; going to Overload state.
4. Overcurrent not present; going back to ON state.
5. Turning OFF the PD.

OFF State

HSSW turn-on is controlled by UVLO, the undervoltage lockout feature. When UVLO is engaged, the HSSW is OFF. In this state, the HSSW is in idle mode, VNEG and HSO pins are disconnected. In normal operation, a complete detect/classification procedure precedes the HSSW turn-on, and the control of this sequence is implemented in the state machine logic of the chip.

INRUSH State

After the controller enables the HSSW, the block starts operation in the INRUSH state. In this state the switch itself is not directly turned on, but operating in a closed-loop current limit mode to avoid high current peaks during the charging of the input capacitor of the dc-dc converter.

If the V_{HSSW} voltage drops below 380 mV (meaning the bypass cap is 99% charged), the HSSW will change state to ON.

ON State

In ON state, the HSSW switch is completely turned on. The HSSW circuit continuously monitors V_{HSSW} . HSSW will change to OVERLOAD state if V_{HSSW} voltage increases over 3.5 V.

OVERLOAD State

In OVERLOAD state the HSSW operates in closed-loop low current limit mode. If the V_{HSSW} voltage drops below 380 mV again, and the HSSW has been in the OVERLOAD state for at least $T_{WAITHSSW}$, the HSSW will change back to the ON state.

2.5 DC-DC Converter

The dc-dc converter is current-controlled for easier compensation and more robust protection of circuit magnetics. The controller has the following features:

- High- and low-side error amplifier (supports Buck and Flyback topologies).
- $<1\ \Omega$ internal switching FET
- Overcurrent detection
- Cycle skipping at low current and short circuit conditions

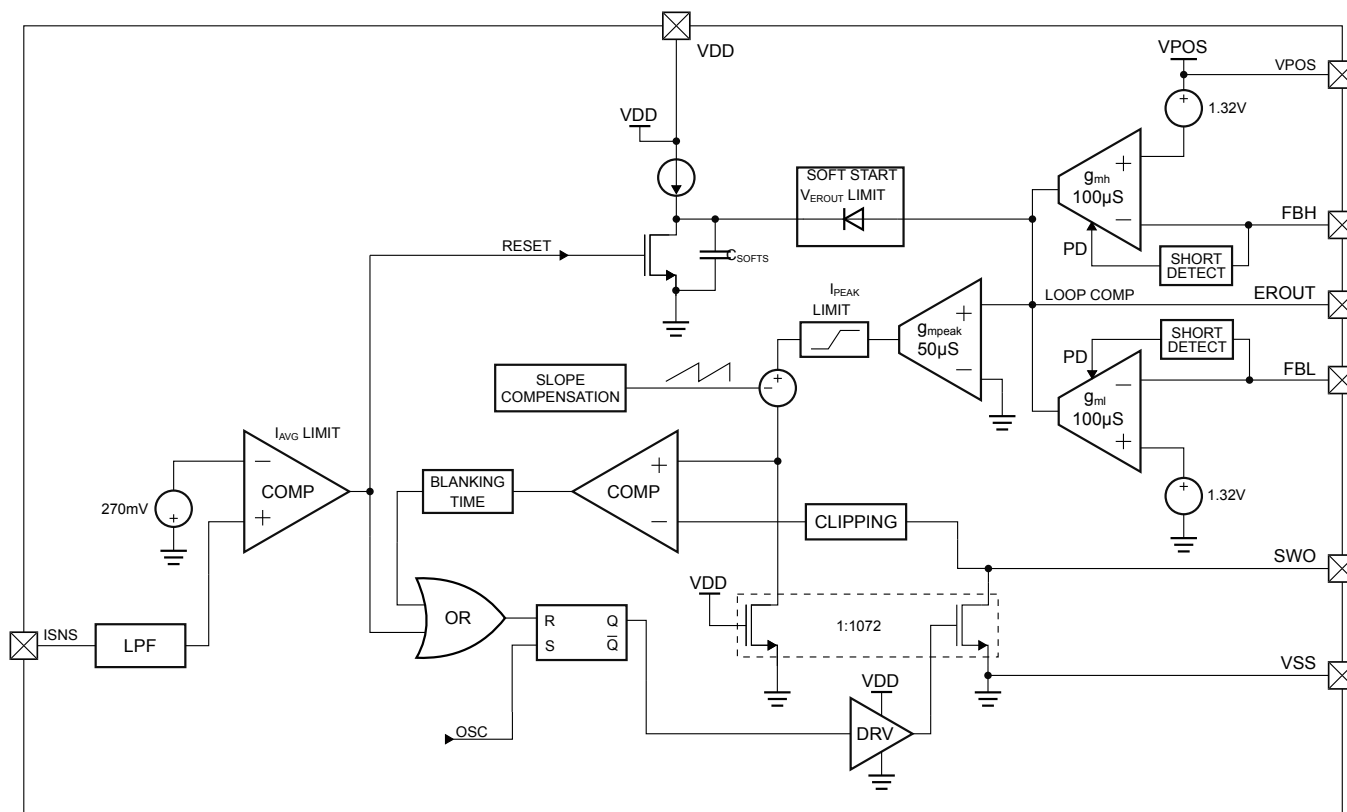


Figure 2.4. Si3404 DC-DC Converter Block Diagram

Feedback to the dc-dc converter can be provided in three ways:

- High side, referenced to VPOS, connected to FBH pin (Buck converter)
- Low side, referenced to VSS, connected to FBL pin (nonisolated Flyback)
- Directly to EROUT pin by a voltage to current converter (isolated Flyback)

The EROUT pin provides current output (if FBL or FBH is used) and voltage input. Also, the loop compensation impedance is connected to EROUT. The active voltage range is V_{EROUT} , which is proportional to the converter peak current.

The converter startup is not configurable; soft start is accomplished by internal circuitry. Soft start time is $T_{SOFTSTART}$. The intelligent soft start circuit dynamically adjusts the soft start time depending on the connected load.

2.5.1 Average Current Sensing, Overcurrent, Low-Current Detection, and Output Short Protection

The application average current is sensed by an external resistor (R_{SENSE}) connected between VSS and ISNS. Overcurrent is detected and triggered when the voltage on the sense resistor exceeds V_{ISNS_OVC} . Sizing the resistor allows the designer to set the overcurrent limit according to application needs. When overcurrent is triggered, the dc-dc controller goes into reset until the overcurrent resolves. When the overcurrent is no longer present, the controller starts up again with softstart.

The Si3404 integrates an output short protection. If the output is shorted for more than 1 ms, the controller will detect a high EROUT signal for more than 1 ms, which will reset the dc-dc controller. A new startup cycle with soft-start turn ON will follow.

2.6 Tunable Oscillator

The dc-dc frequency can be fixed to 250 kHz or tunable by an external resistor.

The tuning resistor must be connected between the R_{FREQ} pin and VPOS. If R_{FREQ} is shorted to VPOS, the fixed frequency oscillator will provide the clock, F_{OSCINT} , to the dc-dc converter; otherwise, the resistor will determine the frequency as shown in the curve below.

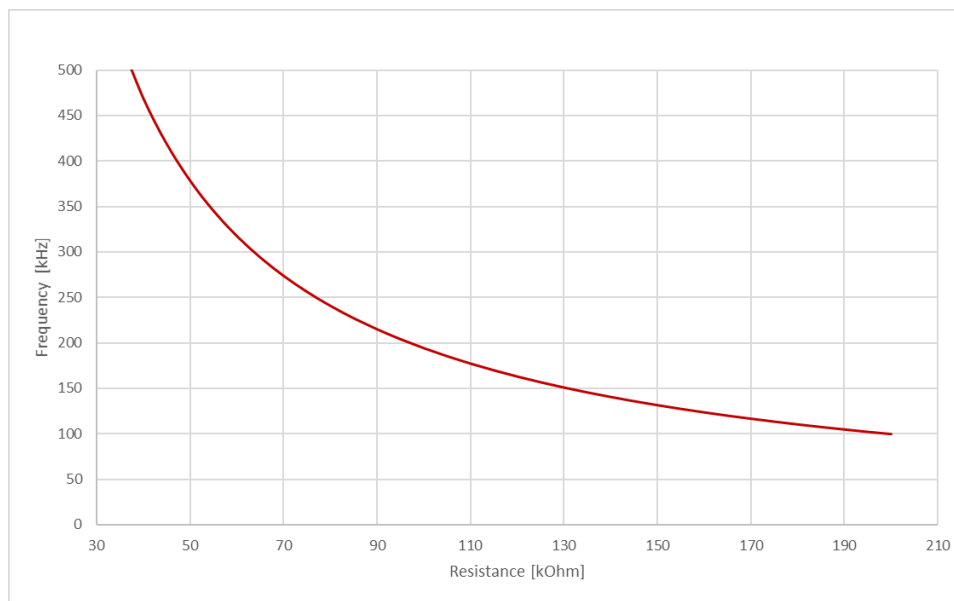


Figure 2.5. R_{FREQ} Frequency Selector Diagram

2.7 Regulators

The chip provides a 5 V output to power LEDs or optocouplers. This is a closed-loop regulator, which ensures accurate output voltage. The 5 V regulator is supplied by an internal 11 V open loop regulator. The 11 V regulator is supplied by a coarse regulator, which is also open-loop. With the Si3404, the VT15 pin can be used to supply this regulator from an optional auxiliary transformer bias winding. The advantage of doing so is additional power saving. The application must be designed to ensure that the absolute maximum rating voltage for the VT15 pin is not exceeded.

2.8 External Wall Adapter Support

The Si3404 allows the use of a range of external wall adapters as a primary or secondary supply. For details on adapter connection, please refer to "AN1130: Using the Si3406/Si34061/Si34062 PoE+ and Si3404 PoE PD Controller In Isolated and Non-Isolated Designs".

3. Application Examples

The following diagrams demonstrate the ease of use and straightforward BOM of the Si3404 Powered Device IC. Detailed reference designs are available in Evaluation KIT User Guides. Also refer to "AN1130: Using the Si3406/Si34061/Si34062 PoE+ and Si3404 PoE PD Controller In Isolated and Non-Isolated Designs".

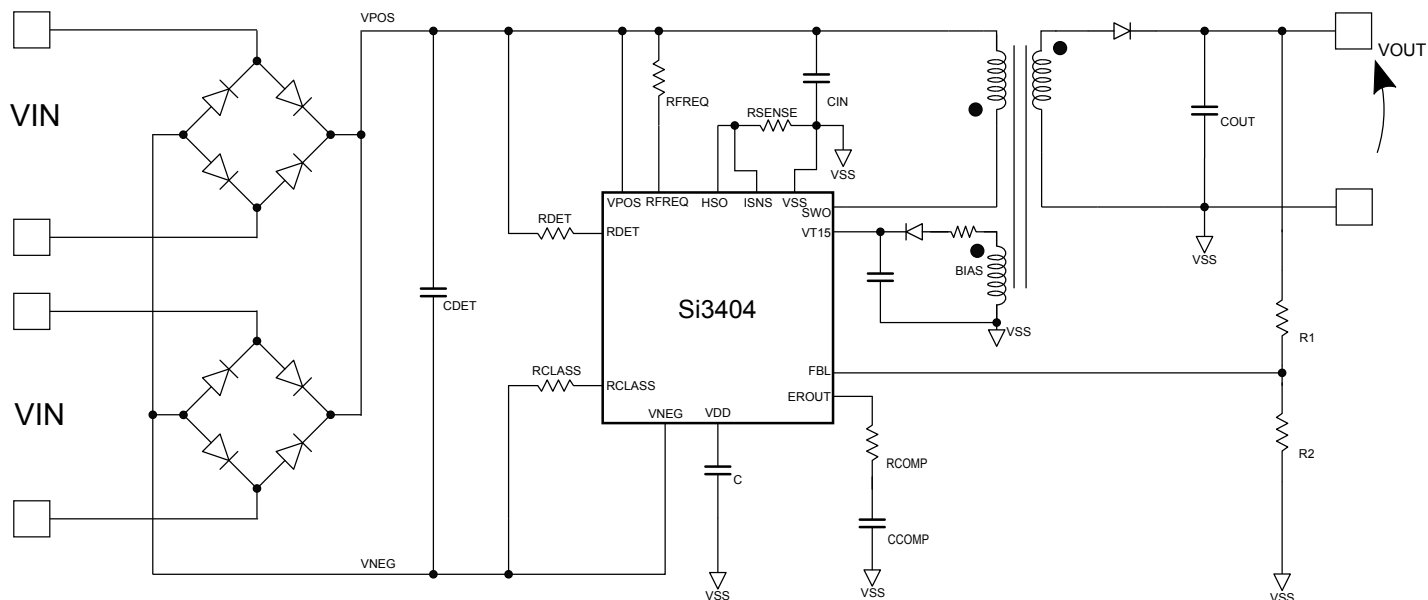


Figure 3.1. Si3404 Non-ISO Flyback Application Diagram

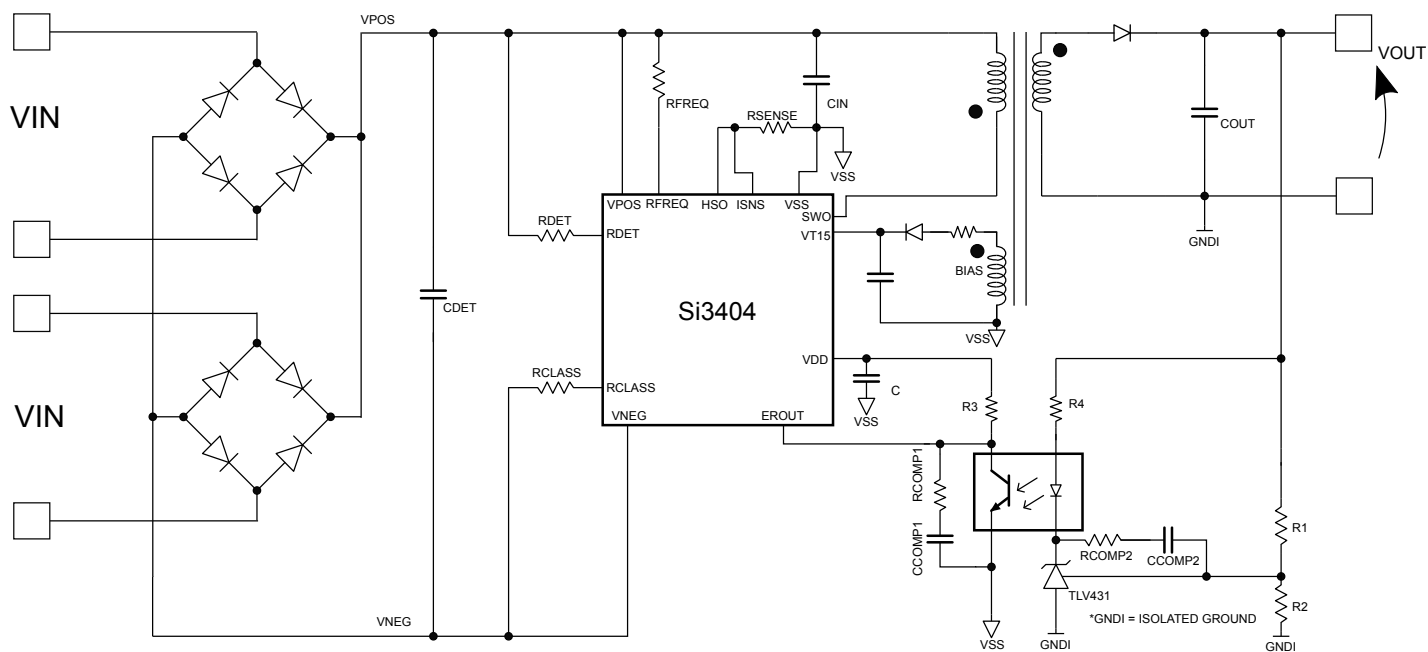


Figure 3.2. Si3404 Isolated Flyback Application Diagram

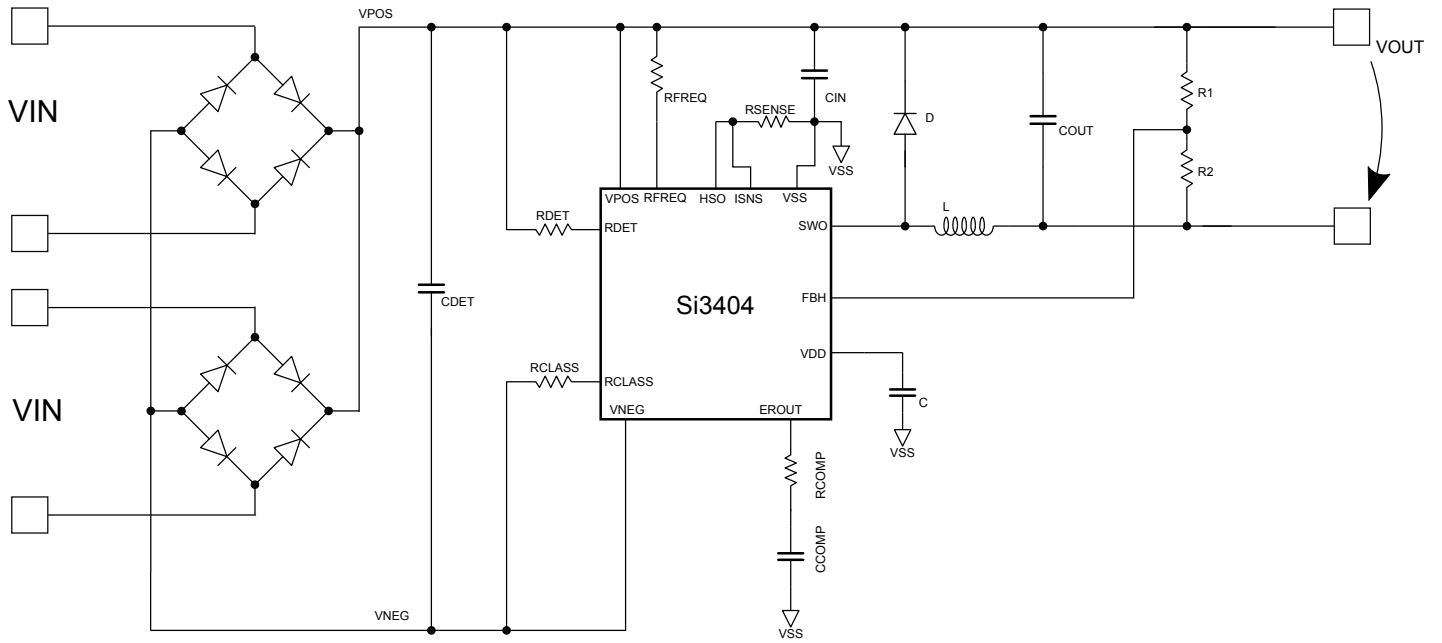


Figure 3.3. Si3404 Buck Application Diagram

4. Electrical Specifications

Table 4.1. Absolute Maximum Ratings¹

Type	Description	Min	Max	Units
Voltage	VNEG-VSS, VPOS- VNEG, HSO ² , RDET ³	-0.7	100	V
	SWO-VSS	-0.7	120	V
	ISNS	-1	1	V
	Low Voltage pins: FBH ³ , EROUT, FBL, RCL ² , RFREQ ³	-0.7	6	V
	Mid Voltage pins: VT15	-0.7	18	V
Peak Current	VPOS ⁴	-5	5	A
Temperature	Storage Temperature	-65	150	°C
	Ambient Operating Temperature	-40	85	

Note:

1. Unless otherwise noted, all voltages referenced to VSS. Permanent device damage may occur if the maximum ratings are exceeded. Functional operation should be restricted to those conditions specified in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may adversely affect device reliability.
2. Voltage referenced to VNEG.
3. Voltage referenced to VPOS.
4. Si340x provides internal protection from certain transient surge voltages on these pins. For more information, refer to "AN1130: Using the Si3406/Si34061/Si34062 PoE+ and Si3404 PoE PD Controller in Isolated and Non-Isolated Designs".

Table 4.2. Recommended Operating Conditions

Symbol	Parameter (Condition)	Min	Typ	Max	Unit
V _{PORT}	V _{PORT} = V _{POS} – V _{NEG}	1.5	—	57	V
V _{HV_OP}	V _{NEG} -V _{SS} , V _{NEG} -H _{SO} , V _{POS} -V _{SS}	1.5	—	57	V
V _{LV_OP}	V _{POS} referred low voltage pins: RFREQ, RDET, FBH	-5.5	—	0	V
V _{LV_OP}	V _{SS} referred low voltage pins: VDD, FBL, ER _{OUT}	0	—	5.5	V
V _{ISNS_OP}	V _{SS} referred current sensing pin: ISNS	-0.5	—	0.5	V
V _{LV_OP}	V _{NEG} referred low voltage pins: RCL	0	—	5.5	V
V _{MV_VT15}	V _{SS} referred medium voltage pin VT15 ¹	12	14.5	16.5	V
I _{AVG}	Allowable continuous current on V _{POS} , SWO, V _{SS} , H _{SO} , V _{NEG}	—	—	600	mA
I _{MAX}	Max current on H _{SO} , V _{NEG} , V _{POS} Max 75 ms 5% Duty Cycle	—	—	683	mA

Note:

- V_{MV_VT15} is relevant for Si3404 only when an external auxiliary bias winding from the primary side of the transformer is being used to improve power conversion efficiency. This can be left undriven, in which case an internal regulator will be used.

Table 4.3. Electrical Characteristics

Symbol	Parameter (Condition)	Min	Typ	Max	Unit
PoE PROTOCOL					
Detection					
V_{DET}	Signature Range (at V_{PORT})	1.5	—	10.1	V
	Signature Resistance (at V_{PORT})	23.75	—	26.25	k Ω
Classification					
V_{RESET}	Classification Reset (at V_{PORT})	0	—	2.81	V
V_{CLASS}	Classification Voltage ON (at V_{PORT})	—	—	14.5	V
	Classification Voltage OFF (at V_{PORT})	20.5	—	—	V
$I_{PortCLASS}$	Class 0 ($R_{CLASS} > 681 \Omega$)	0	—	4	mA
	Class 1 ($R_{CLASS} = 140 \Omega @ 1\%$)	9	—	12	mA
	Class 2 ($R_{CLASS} = 75 \Omega @ 1\%$)	17	—	20	mA
	Class 3 ($R_{CLASS} = 48.7 \Omega @ 1\%$)	26	—	30	mA
Power On and UVLO					
V_{UVLO_R}	Hotswap closed and converter on	34	37	40	V
V_{UVLO_F}	Hotswap open and converter off	30	32	34	V
V_{UVLO_HYST}		3.5	4.5	6	V
Thermal Characteristics					
T_{shd}	Thermal shutdown	—	160	—	$^{\circ}\text{C}$
T_{HYST}	Thermal shutdown hysteresis	—	20	—	$^{\circ}\text{C}$
On-Chip Transient Voltage Suppression/Protection					
V_{PROT}	TVS protection activation voltage (V_{POS} - V_{NEG})	100	—	—	V
Hotswap Switch					
I_{inrush}	Inrush current	100	170	200	mA
$I_{MAXHSSW}$	Maximum continuous operating current	—	—	600	mA
V_{HSSW_ON}	Switch ON voltage	—	380	—	mV
V_{HSSW_OFF}	Switch OFF voltage, HSSW goes to overload cycle	—	3.5	—	V
I_{OVL}	Switch current limit in OVERLOAD State	—	10.5	—	mA
$T_{WAITHSSW}$	Wait time in OVERLOAD	80	96	116	ms
R_{ONHSSW}	Internal hotswap drain-source resistance while ON	0.65	1.5	2.9	Ω
DC-DC					

Symbol	Parameter (Condition)	Min	Typ	Max	Unit
I _{SWOPEAK}	Peak current limit of internal FET (SWO pin)	2.1	—	2.7	A
F _{OSCINT}	Using internal Oscillator	215	250	290	kHz
F _{OSCEXT}	Using external Oscillator, RFREQ = 215 kΩ	75	95	115	kHz
	Using external Oscillator, RFREQ = 39 kΩ	420	470	520	kHz
DUC	Output duty cycle of PWM	—	—	75	%
V _{FBREF}	FBH (referenced to VPOS) and FBL (referenced to VSS) reference voltage	1.28	1.32	1.36	V
V _{EROUT}	Operating voltage range of error input	1	—	4	V
T _{HICCUP}	Output short protection if EROUT is max	—	1	—	ms
V _{ISNS_OVC}	Overcurrent limit voltage on ISNS (ref. to VSS)	−305	−270	−255	mV
T _{SOFTSTART}	Startup time ¹	—	15	—	ms
R _{ONDCCDC}	Internal dc-dc switching FET drain-source resistance while ON	—	0.9	1.2	Ω
Regulators					
VT15	Override internal regulator with transformer winding	12.5	—	16.5	V
VDD	5 V regulated output	4.9	5.2	5.5	V
VDD _{ILIM}	dc current limit of VDD	9.7	11.2	—	mA
C _{REG}	Filter capacitor on VDD	82	100	220	nF
Power Dissipation					
P _{INTMAX}	dc-dc max power internal FET	—	0.5	0.9	W
I _{PortOP}	Operating current (V _{PORT} 57 V; 250 kHz)	—	3	5	mA
Package Thermal Characteristics					
θ _{JA-EFF}	QFN20 ²	—	46.8	—	C°/W
Note:					
1. Depends on output load.					
2. Assumes 4-Layer PCB with adequate layout.					

5. Pin Descriptions

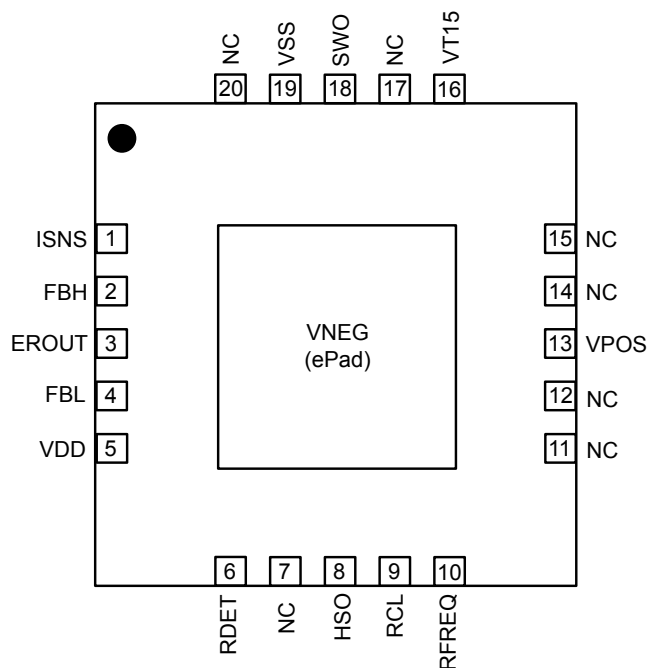


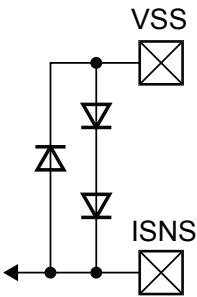
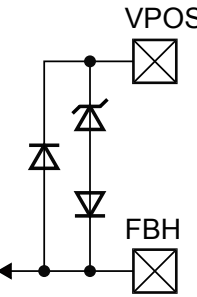
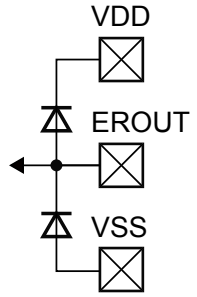
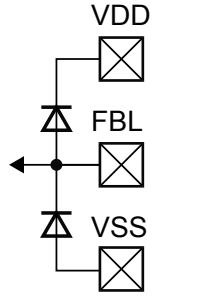
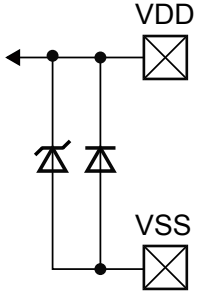
Figure 5.1. Si3404 Pinout

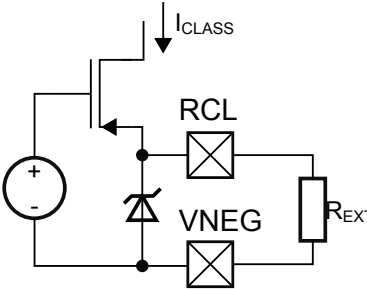
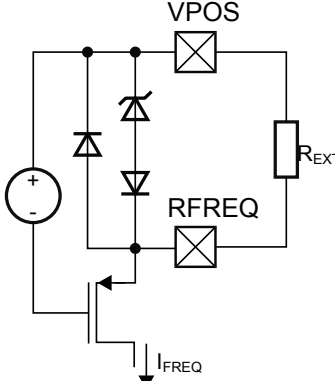
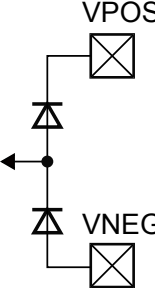
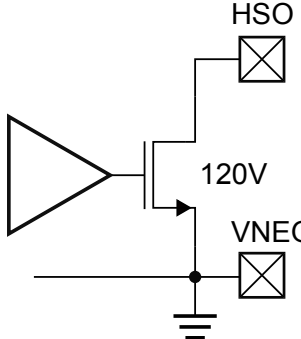
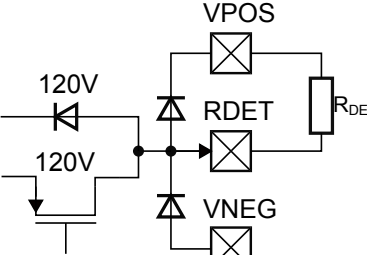
Table 5.1. Pin Descriptions

Si3404 Pins	Name	Ref	Dir.	Vrange	Description
1	ISNS	VSS	I	-0.5 to 0	Chip current sense resistor input
2	FBH	VPOS	I	0–5.5	High side (VPOS referred) dc-dc feedback (Buck converter)
3	EROUT	VSS	IO	0–5.5	Error amplifier current output, compensation impedance input
4	FBL	VSS	I	0–5.5	Low side (VSS referenced) dc-dc feedback (Flyback converter)
5	VDD	VSS	O	0–5.5	5 V regulator output
6	RDET	VPOS	IO	0–100	Detection resistor
8	HSO	VNEG	IO	0–100	Hotswap switch output
9	RCL	VNEG	IO	0–5.5	Classification resistor
10	RFREQ	VPOS	IO	0–5.5	Oscillator frequency tuning resistor, tie to VPOS to select default frequency
13	VPOS	—	IO	0–100	Rectified high-voltage supply positive rail
16	VT15	VSS	I	0–16.5	dc-dc transformer auxiliary winding input
18	SWO	VSS	O	0–120	Internal dc-dc switch output (NMOS drain)
19	VSS	—	IO	0	dc-dc converter primary ground
ePad	VNEG	—	IO	0	Rectified high voltage supply ground
7, 11, 12, 14, 15, 17, 20	NC	—	—	—	Connect to VNEG for better thermal performance

5.1 Detailed Pin Descriptions

Table 5.2. Circuit Equivalent and Description of Die Pads

Pin Name	Detailed Description	Circuit Detail
ISNS	Average current sense resistor input. The resistor value will set the maximum allowed current for the application. The overcurrent threshold voltage V_{ISNS_OVC} . Note that this pin voltage goes below VSS.	
FBH	High side dc-dc feedback input. Need to be tied to VPOS when not used. See VFBREF.	
EROUT	dc-dc converter error output; current out, voltage sense. Loop compensating impedance should be connected here. $I_{EROUT} = (V_{FBH} - V_{FBREF}) \times 50 \mu A$ or $I_{EROUT} = (V_{FBL} - V_{FBREF}) \times 50 \mu A$	
FBL	Low side dc-dc feedback input. Need to be tied to VSS when not used. See VFBREF	
VDD	Regulated 5 V relative to VSS. There is no foldback characteristic, reaching VDD_{ILIM} the output voltage decreases. The regulator needs C_{REG} external capacitance.	

Pin Name	Detailed Description	Circuit Detail
RCL	Classification resistor input. For class 0 this pin can be left floating. Pin is active only at time of classification.	
RFREQ	Used for adjusting the oscillator frequency. The frequency is inversely proportional to the value of the connected resistor.	
VPOS, VNEG	Main chip input power. Note that VNEG (the ePad on the bottom of the chip) also provides thermal relief.	
HSO	Hotswap Switch Output. The switch shorts the VNEG and HSO pins, and includes several other functions. See hotswap switch section for details.	
RDET	The user has to tie the RDET resistor between this pin and VPOS. During detection, a high voltage switch pulls down RDET to VNEG. After detection, the reference block uses RDET as absolute chip current reference, forcing -750 mV relative to VPOS, creating 30 μA for the internal blocks.	

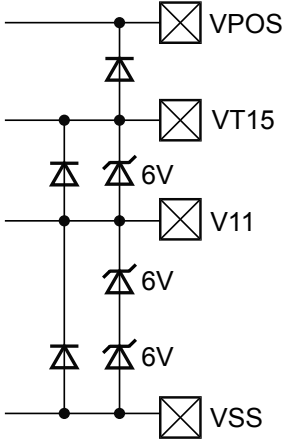
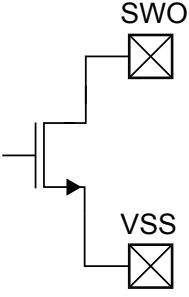
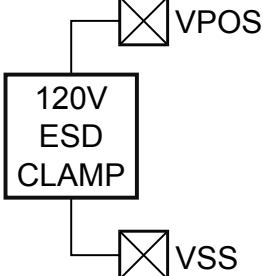
Pin Name	Detailed Description	Circuit Detail
VT15	<p>VT15 is input for an optional 15 V supply generated by an auxiliary transformer bias winding. If the bias winding voltage is lower than VT15_MIN, the internal 15 V coarse regulator will provide the current for the 11 V regulator. V11 is not available on the Si3404 but is included to show internal connections.</p>	
SWO	<p>dc-dc converter switching transistor drain output, $V_{max} = 120\text{ V}$.</p>	
VSS	<p>dc-dc converter ground.</p>	

Table 6.1. Package Diagram Dimensions

Dimension	Min	Nom	Max
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
b	0.18	0.25	0.30
D	4.00 BSC.		
D2	2.55	2.60	2.65
e	0.50 BSC.		
E	4.00 BSC.		
E2	2.50	2.60	2.70
L	0.30	0.40	0.50
aaa	—	—	0.10
bbb	—	—	0.10
ccc	—	—	0.08
ddd	—	—	0.10
eee	—	—	0.10

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This drawing conforms to the JEDEC Solid State Outline MO-220, Variation VGGD-8.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

6.2 Land Pattern: Si3404

The figure below illustrates the land pattern details for the Si3404. The table lists the values for the dimensions shown in the illustration.

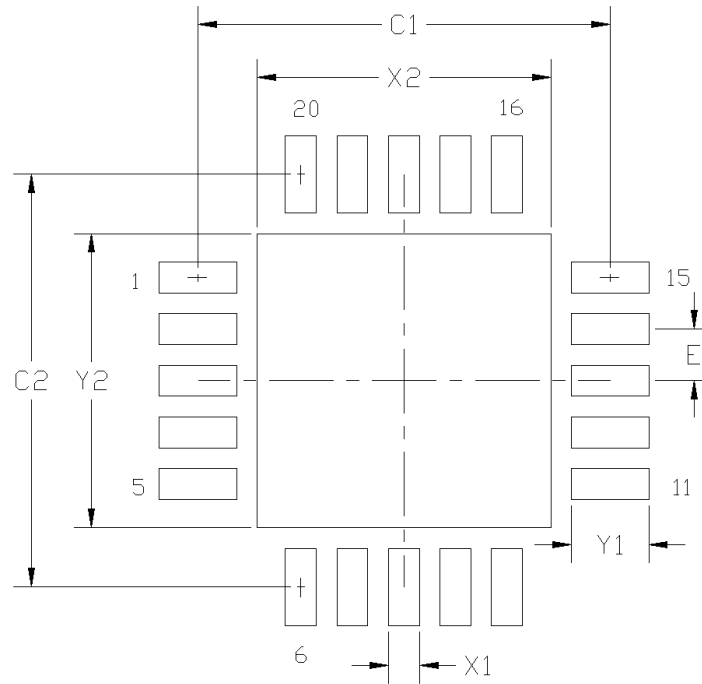


Figure 6.2. 20-Pin, QFN Land Pattern

Table 6.2. Land Pattern Dimensions

Dimension	Min	Max
C1	3.90	4.00
C2	3.90	4.00
E	0.50 BSC	
X1	0.20	0.30
X2	2.55	2.65
Y1	0.65	0.75
Y2	2.55	2.65

Note:**General**

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This land pattern design is based on the IPC-7351 guidelines.

Solder Mask Design

1. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 μ m minimum, all the way around the pad.

Stencil Design

1. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
2. The stencil thickness should be 0.125 mm (5 mils).
3. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads.
4. A 2x2 array of 1.10 mm x 1.10 mm openings on 1.30 mm pitch should be used for the center ground pad.

Card Assembly

1. A No-Clean, Type-3 solder paste is recommended.
2. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

7. Si3404 Top Marking

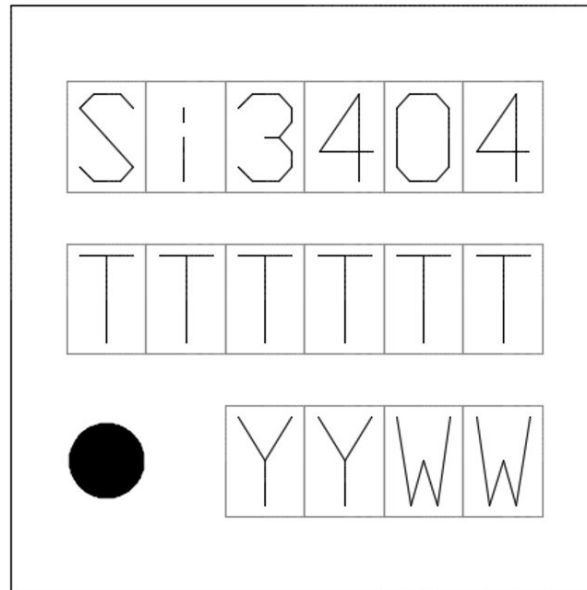


Figure 7.1. Si3404 Top Marking

Table 7.1. Si3404 Top Marking Explanation

Mark Method:	Laser	
Pin 1 Mark:	Circle = 0.50 mm Diameter (Lower-Left Corner)	
Font Size:	0.6 Point (24 mils)	
Line 1 Mark Format:	Device Part Number	Si3404
Line 2 Mark Format:	TTTTTT	Trace code from the Assembly Purchase Order form
Line 3 Mark Format:	YY = Year WW = Work Week	Assembly Year Assembly Week

8. Revision History

Revision 1.0

July, 2018

- Updated [Figure 2.2 Powered Device Voltages on page 5](#).
 - Removed Type 2 signaling from diagram.
- Updated [Figure 2.3 Hotswap Switch 4-State Machine on page 6](#).
 - Clearer state transition diagram and improved transition descriptions.
- Updated [2.5.1 Average Current Sensing, Overcurrent, Low-Current Detection, and Output Short Protection](#).
 - Added information on output short protection.
- Updated [Table 4.1 Absolute Maximum Ratings¹ on page 11](#).
 - Added min and max current for VPOS.
 - Added note about internal surge protection.
- Updated [Table 4.2 Recommended Operating Conditions on page 12](#).
 - Added VPOS to I_{AVG} spec; changed I_{PEAK} to I_{MAX} , and removed SWO and VSS from specification.
- Updated [Table 4.3 Electrical Characteristics on page 13](#).
 - Updated V_{DET} spec to include low threshold and high threshold specs.
 - Updated classification reset max voltage (V_{RESET}) based on final characterization data.
 - Updated classification voltage V_{CLASS} based on final characterization data.
 - Added max and min V_{UVLO_R} , V_{UVLO_F} , and V_{UVLO_HYST} max and min voltages.
 - Removed I_{OVL} max and min current.
 - Added min and max frequency to F_{OSCINT} based on final characterization data.
 - Removed “TBD” from DUC spec.
 - Added max and min V_{FBREF} voltage.
 - Added T_{HICCUP} typical spec.
 - Added max and min V_{ISNS_OVC} voltage.
 - Updated $T_{SOFTSTART}$ time based on application data and added note about dependence on output load.
 - Updated min VT15 based on characterization data.
 - Updated VDD min, typ, and max based on final characterization data.
 - Added VDD_{LIM} max voltage.
 - Added min and max C_{REG} capacitance.
 - Updated P_{INTMAX} based on final characterization data.
 - Removed P_{MAX} spec.
 - Updated I_{PORTOP} max current based on final characterization data.
- Updated [Table 5.1 Pin Descriptions on page 15](#).
 - Updated Vrange.
- Updated [Table 5.2 Circuit Equivalent and Description of Die Pads on page 16](#).
 - Added detail to VT15 pin description.

Revision 0.5

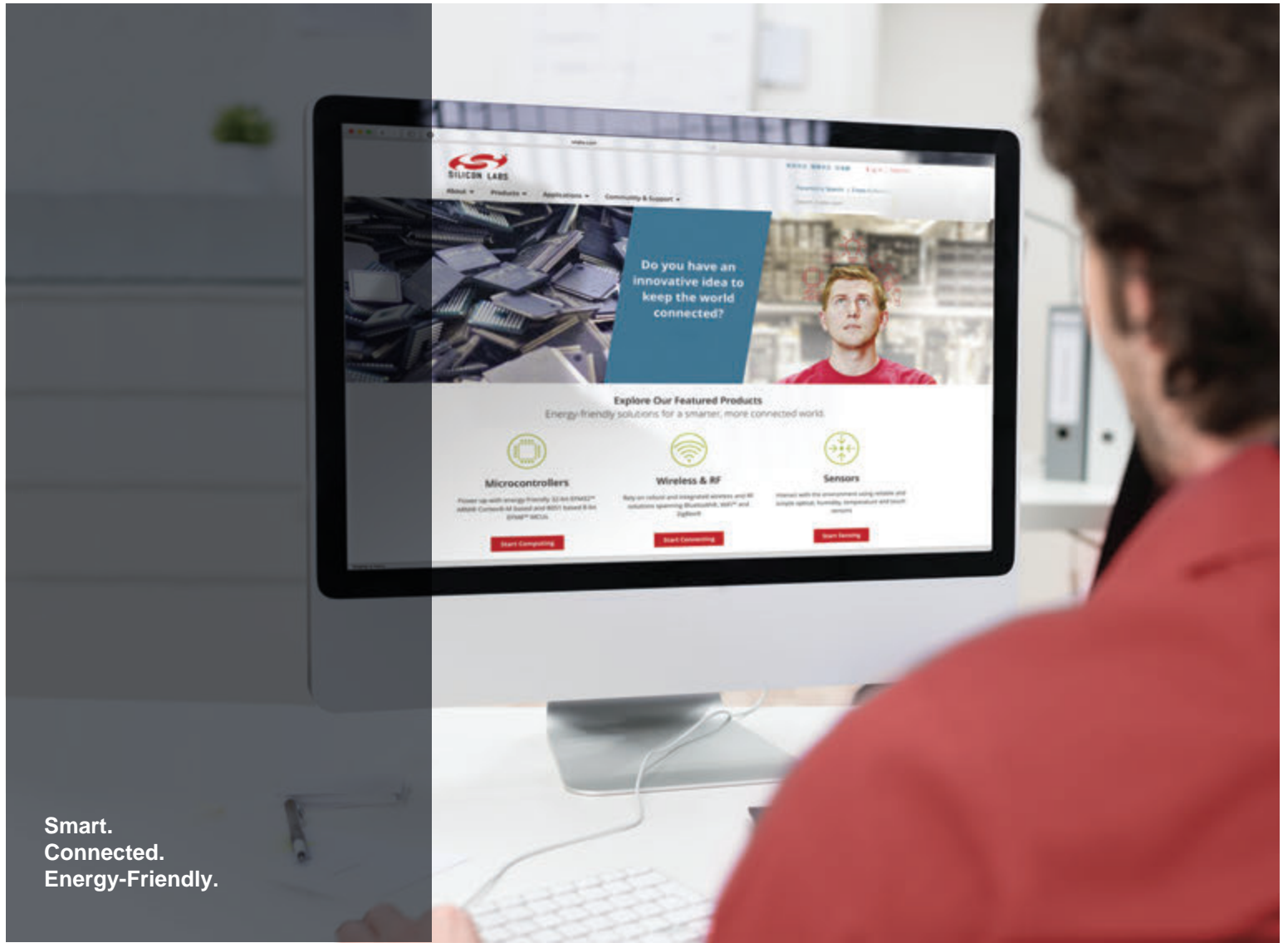
February, 2018

- Updated [2. System Overview](#) and [3. Application Examples](#).
 - Added theory of operation and application content.
- Updated [Table 4.1 Absolute Maximum Ratings¹ on page 11](#), [Table 4.2 Recommended Operating Conditions on page 12](#), and [Table 4.3 Electrical Characteristics on page 13](#).
 - Clarified multiple parameters.
- Added [5.1 Detailed Pin Descriptions](#).
- Added [6. Packaging](#) including outline and land pattern.

Revision 0.1

March, 2017

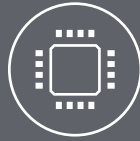
- Initial release.



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